SEMICONDUCTOR

DATA SHEET

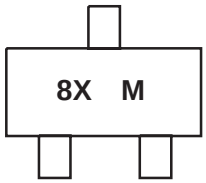
MUN521 Series

Bias Resistor Transistor

NPN Silicon Surface Mount Transistor with Monolithic Bias Resistor Network

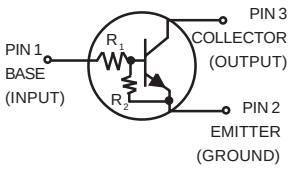
SC-70 / SOT-323

MARKING DIAGRAM



8x = Specific Device Code
x = (See Marking Table)
M= Date Code

This new series of digital transistors is designed to replace a single device and its external resistor bias network. The BRT (Bias Resistor Transistor) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base–emitter resistor. The BRT eliminates these individual components by integrating them into a single device. The use of a BRT can reduce both system cost and board space. The device is housed in the SC–70/SOT–323 package which is designed for low power surface mount applications.



- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- The SC–70/SOT–323 package can be soldered using wave or reflow. The modified gull–winged leads absorb thermal stress during soldering eliminating the possibility of damage to the die.
- Available in 8 mm embossed tape and reel
  Use the Device Number to order the 7 inch/3000 unit reel.
- Pb-Free package is available

MAXIMUM RATINGS (T_A = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	50	Vdc
Collector-Emitter Voltage	V_{CEO}	50	Vdc
Collector Current	I_C	100	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation T_A = 25°C Derate above 25°C	P_D	202 (Note 1.) 310 (Note 2.) 1.6 (Note 1.) 2.5 (Note 2.)	mW mW/°C
Thermal Resistance – Junction-to-Ambient	$R_{\theta JA}$	618 (Note 1.) 403 (Note 2.)	°C/W
Thermal Resistance – Junction-to-Lead	$R_{\theta JL}$	280 (Note 1.) 332 (Note 2.)	°C/W
Junction and Storage Temperature Range	T_J, T_{stg}	–55 to +150	°C

1. FR–4 @ Minimum Pad
2. FR–4 @ 1.0 x 1.0 inch Pad

DEVICE MARKING RESISTOR VALUES AND ORDERING INFORMATION

Device	Package	Marking	R1(K)	R2(K)	Shipping
MUN5211	SC-70/SOT-323	8A	10	10	3000/Tape&Reel
MUN5212	SC-70/SOT-323	8B	22	22	3000/Tape&Reel
MUN5213	SC-70/SOT-323	8C	47	47	3000/Tape&Reel
MUN5214	SC-70/SOT-323	8D	10	47	3000/Tape&Reel
MUN5215(Note 3)	SC-70/SOT-323	8E	10	∞	3000/Tape&Reel
MUN5216(Note 3)	SC-70/SOT-323	8F	4.7	∞	3000/Tape&Reel
MUN5230(Note 3)	SC-70/SOT-323	8G	1	1	3000/Tape&Reel
MUN5231(Note 3)	SC-70/SOT-323	8H	2.2	2.2	3000/Tape&Reel
MUN5232(Note 3)	SC-70/SOT-323	8J	4.7	4.7	3000/Tape&Reel
MUN5233(Note 3)	SC-70/SOT-323	8K	4.7	47	3000/Tape&Reel
MUN5234(Note 3)	SC-70/SOT-323	8L	22	47	3000/Tape&Reel
MUN5235(Note 3)	SC-70/SOT-323	8M	2.2	47	3000/Tape&Reel
MUN5236(Note 3)	SC-70/SOT-323	8N	100	100	3000/Tape&Reel
MUN5237(Note 3)	SC-70/SOT-323	8P	47	22	3000/Tape&Reel

3. New devices. Updated curves to follow in subsequent data sheets.

ELECTRICAL CHARACTERISTICS

MUN521 Series

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector-Base Cutoff Current (V_{CB} = 50 V, I_E = 0)		I_{CBO}	–	–	100	nAdc
Collector-Emitter Cutoff Current (V_{CE} = 50 V, I_B = 0)		I_{CEO}	–	–	500	nAdc
Emitter-Base Cutoff Current	MUN5211	I_{EBO}	–	–	0.5	mAdc
(V_{EB} = 6.0 V, I_C = 0)	MUN5212		–	–	0.2	
	MUN5213		–	–	0.1	
	MUN5214		–	–	0.2	
	MUN5215		–	–	0.9	
	MUN5216		–	–	1.9	
	MUN5230		–	–	4.3	
	MUN5231		–	–	2.3	
	MUN5232		–	–	1.5	
	MUN5233		–	–	0.18	
	MUN5234		–	–	0.13	
	MUN5235		–	–	0.2	
	MUN5236		–	–	0.05	
	MUN5237		–	–	0.13	
Collector-Base Breakdown Voltage (I_C = 10 μA, I_E = 0)		$V_{(BR)CBO}$	50	–	–	Vdc
Collector-Emitter Breakdown Voltage (Note 4.) (I_C = 2.0 mA, I_B = 0)		$V_{(BR)CEO}$	50	–	–	Vdc
ON CHARACTERISTICS (Note 4.)						
DC Current GainMUN5211T1		h_{FE}	35	60	–	
(V_{CE} = 10 V, I_C = 5.0 mA)MUN5212T1			60	100	–	
	MUN5213		80	140	–	
	MUN5214		80	140	–	
	MUN5215		160	350	–	
	MUN5216		160	350	–	
	MUN5230		3.0	5.0	–	
	MUN5231		8.0	15	–	
	MUN5232		15	30	–	
	MUN5233		80	200	–	
	MUN5234		80	150	–	
	MUN5235		80	140	–	
	MUN5236		80	150	–	
	MUN5237		80	140	–	
Collector-Emitter Saturation Voltage (I_C = 10 mA, I_B = 0.3 mA) (I_C = 10 mA, I_B = 5 mA)MUN5230/MUN5231 (I_C = 10 mA, I_B = 1 mA)MUN5215/MUN5216/ MUN5232/MUN5233/MUN5234		$V_{CE(sat)}$	–	–	0.25	Vdc
Output Voltage (on)		V_{OL}				Vdc
(V_{CC} = 5.0 V, V_B = 2.5 V, R_L = 1.0 kΩ)	MUN5211		–	–	0.2	
	MUN5212		–	–	0.2	
	MUN5214		–	–	0.2	
	MUN5215		–	–	0.2	
	MUN5216		–	–	0.2	
	MUN5230		–	–	0.2	
	MUN5231		–	–	0.2	
	MUN5232		–	–	0.2	
	MUN5233		–	–	0.2	
	MUN5234		–	–	0.2	
	MUN5235		–	–	0.2	
(V_{CC} = 5.0 V, V_B = 3.5 V, R_L = 1.0 kΩ	MUN5213		–	–	0.2	
(V_{CC} = 5.0 V, V_B = 5.5 V, R_L = 1.0 kΩ	MUN5236		–	–	0.2	
(V_{CC} = 5.0 V, V_B = 4.0 V, R_L = 1.0 kΩ	MUN5237		–	–	0.2	

4. Pulse Test: Pulse Width < 300 μs, Duty Cycle < 2.0%

ELECTRICAL CHARACTERISTICS

MUN521 Series

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted) (Continued)

Characteristic		Symbol	Min	Typ	Max	Unit
ON CHARACTERISTICS (Note 5.) (Continued)						
Output Voltage (off) (V_{CC} = 5.0 V, V_B = 0.5 V, R_L = 1.0 kΩ) (V_{CC} = 5.0 V, V_B = 0.050 V, R_L = 1.0 kΩ (V_{CC} = 5.0 V, V_B = 0.25 V, R_L = 1.0 kΩ	MUN5230 MUN5215 MUN5216 MUN5233	V_{OH}	4.9	–	–	Vdc
Input Resistor	MUN5211	R_1	7.0	10	13	kΩ
	MUN5212		15.4	22	28.6	
	MUN5213		32.9	47	61.1	
	MUN5214		7.0	10	13	
	MUN5215		7.0	10	13	
	MUN5216		3.3	4.7	6.1	
	MUN5230		0.7	1.0	1.3	
	MUN5231		1.5	2.2	2.9	
	MUN5232		3.3	4.7	6.1	
	MUN5233		3.3	4.7	6.1	
	MUN5234		15.4	22	28.6	
	MUN5235		1.54	2.2	2.86	
	MUN5236		70	100	130	
	MUN5237		32.9	47	61.1	
Resistor Rati	MUN5211/MUN5212/MUN5213	R_1/R_2				
	MUN5236		0.8	1.0	1.2	
	MUN5214		0.17	0.21	0.25	
	MUN5215/MUN5216		–	–	–	
	MUN5230/MUN5231/MUN5232		0.8	1.0	1.2	
	MUN5233		0.055	0.1	0.185	
	MUN5234		0.38	0.47	0.56	
	MUN5235		0.038	0.047	0.056	
	MUN5237		1.7	2.1	2.6	

5. Pulse Test: Pulse Width < 300 μs, Duty Cycle < 2.0%

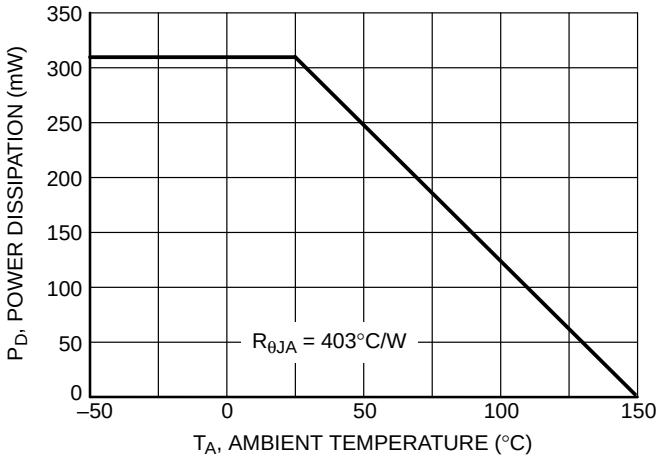


Figure 1. Derating Curve

DEVICE CHARACTERISTICS

MUN521 Series

TYPICAL ELECTRICAL CHARACTERISTICS – MUN5211

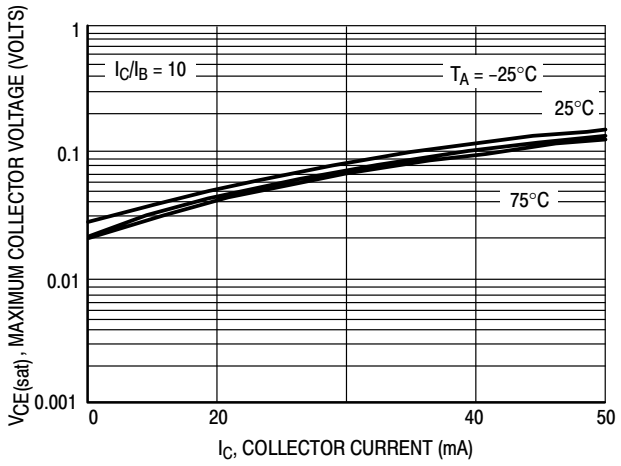


Figure 2. $V_{CE(sat)}$ versus I_C

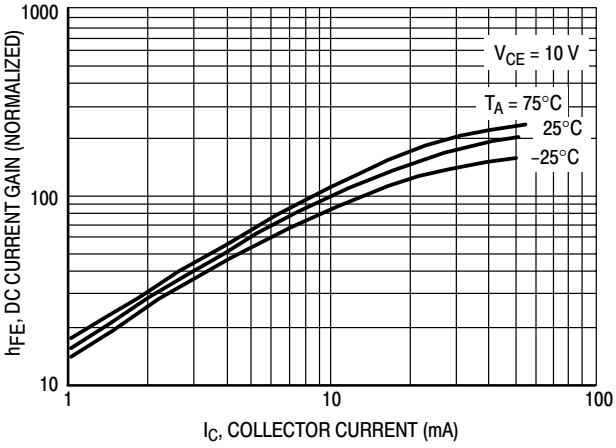


Figure 3. DC Current Gain

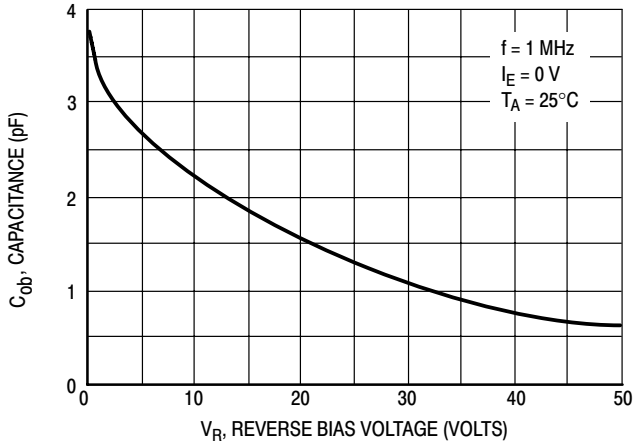


Figure 4. Output Capacitance

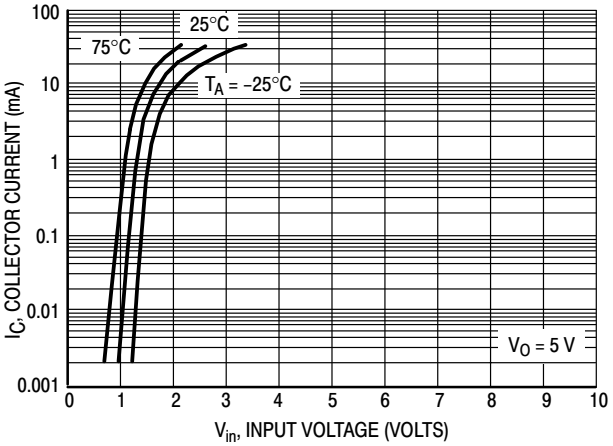


Figure 5. Output Current versus Input Voltage

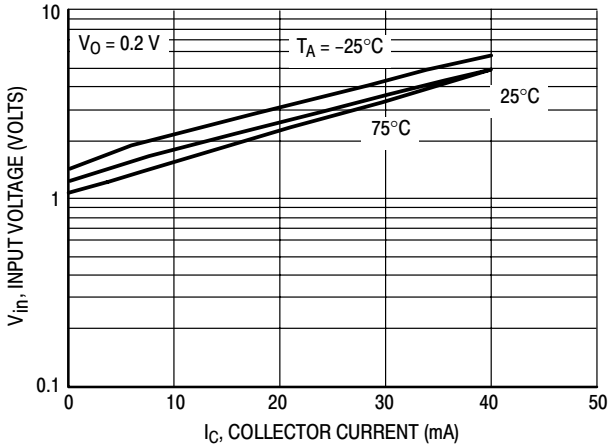


Figure 6. Input Voltage versus Output Current

DEVICE CHARACTERISTICS

MUN521 Series

TYPICAL ELECTRICAL CHARACTERISTICS – MUN5212

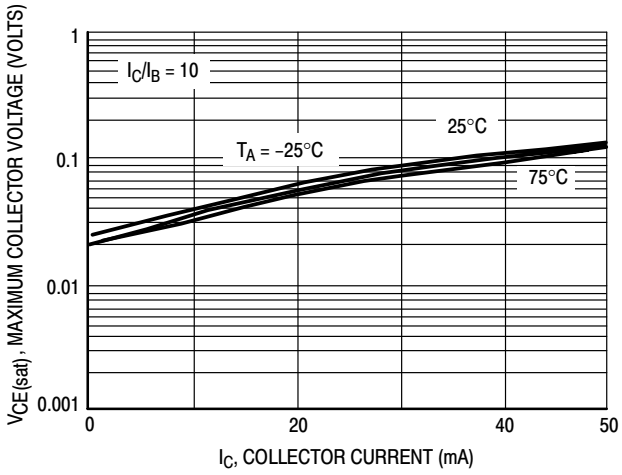


Figure 7. $V_{CE(sat)}$ versus I_C

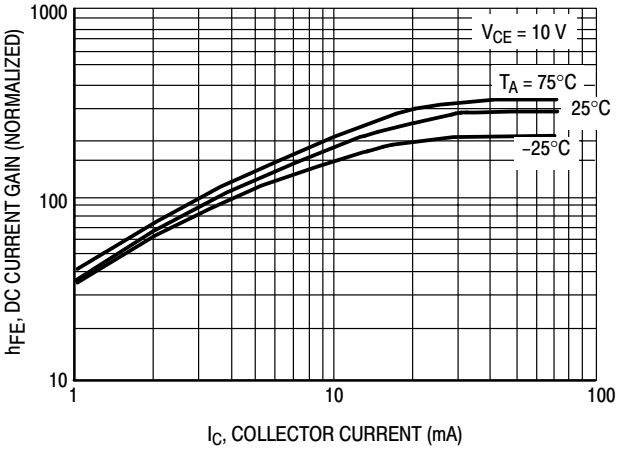


Figure 8. DC Current Gain

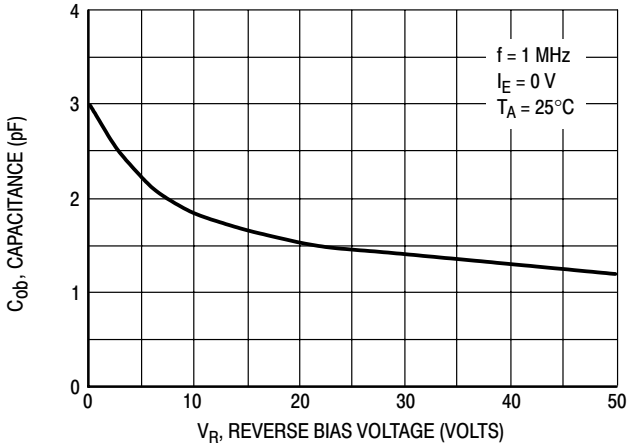


Figure 9. Output Capacitance

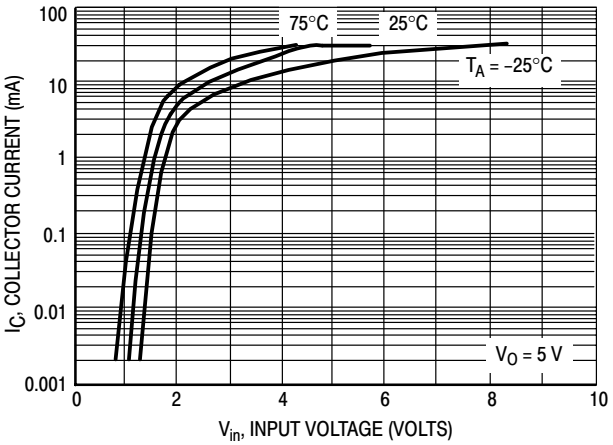


Figure 10. Output Current versus Input Voltage

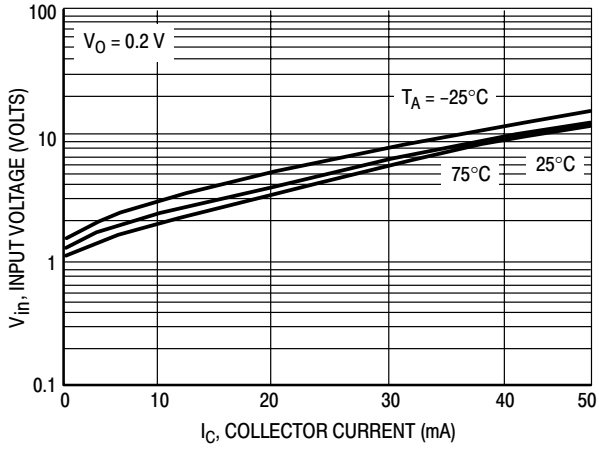


Figure 11. Input Voltage versus Output Current

DEVICE CHARACTERISTICS

MUN521 Series

TYPICAL ELECTRICAL CHARACTERISTICS – MUN5213

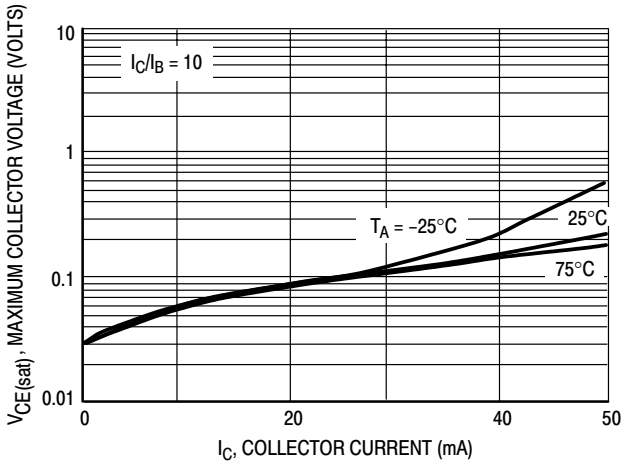


Figure 12. $V_{CE(sat)}$ versus I_C

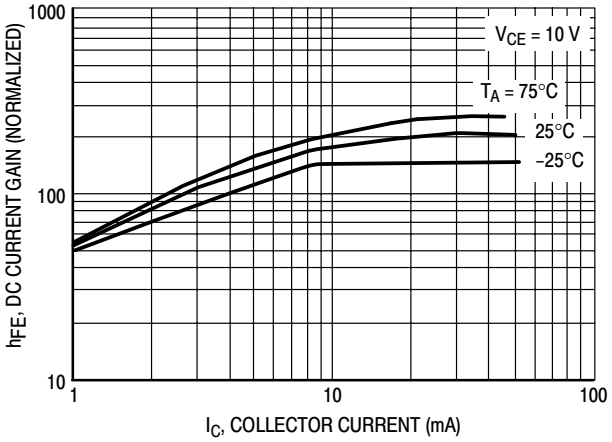


Figure 13. DC Current Gain

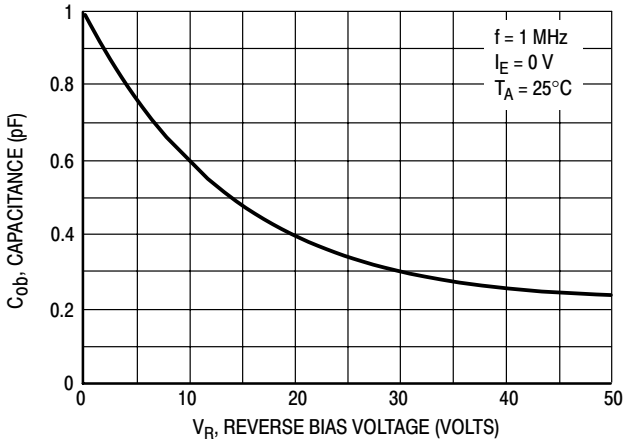


Figure 14. Output Capacitance

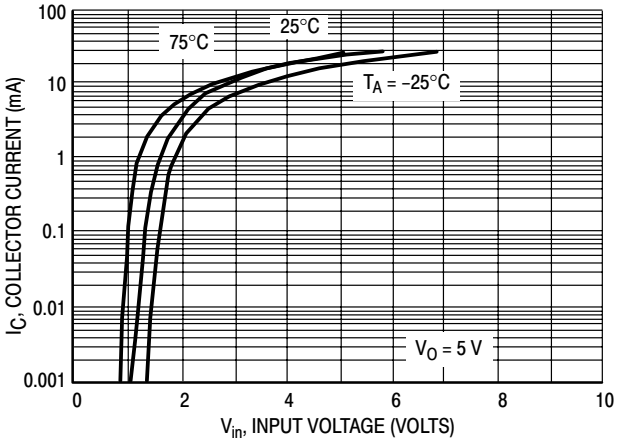


Figure 15. Output Current versus Input Voltage

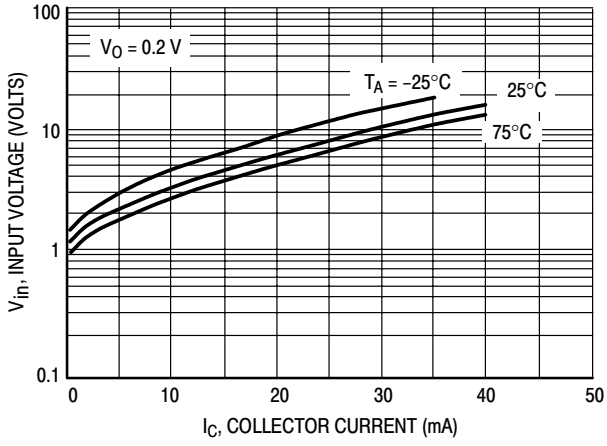


Figure 16. Input Voltage versus Output Current

DEVICE CHARACTERISTICS

MUN521 Series

TYPICAL ELECTRICAL CHARACTERISTICS – MUN5214

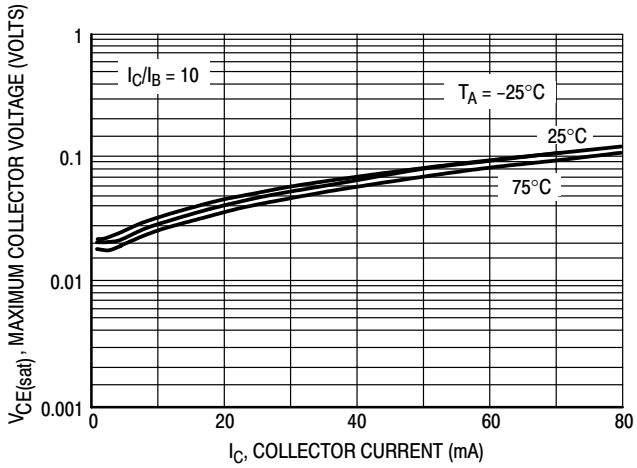


Figure 17. $V_{CE(sat)}$ versus I_C

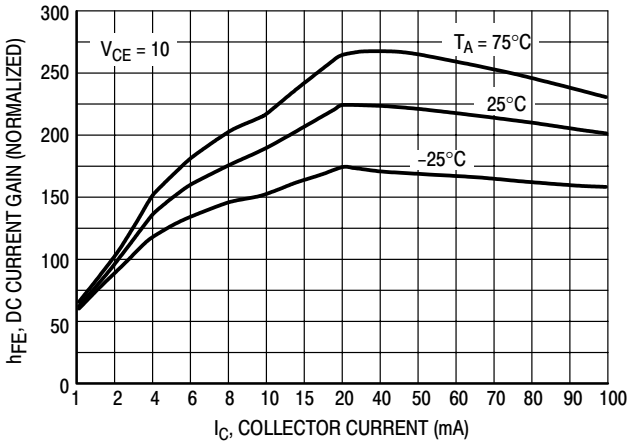


Figure 18. DC Current Gain

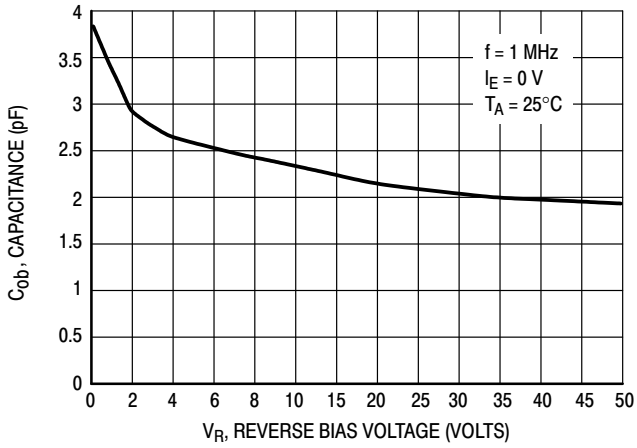


Figure 19. Output Capacitance

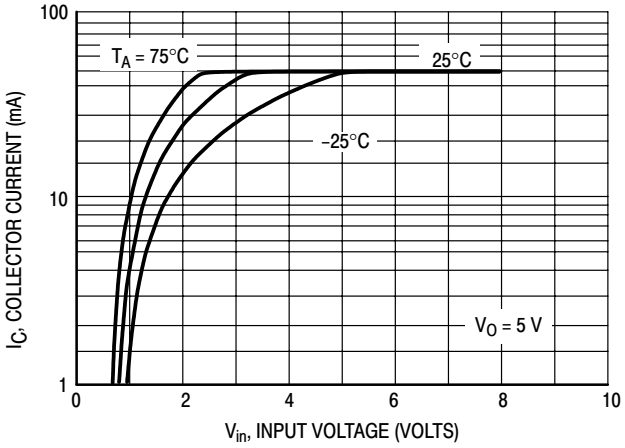


Figure 20. Output Current versus Input Voltage

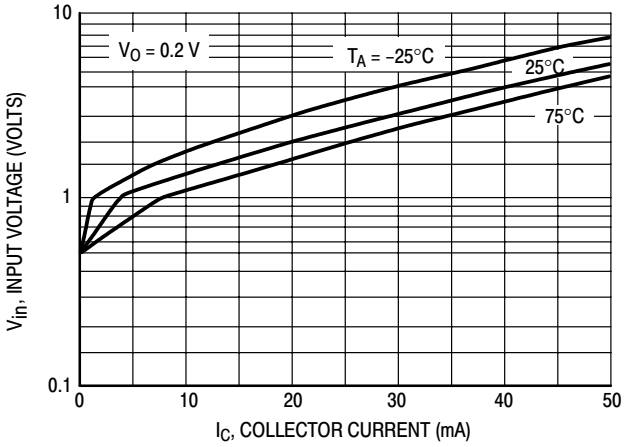


Figure 21. Input Voltage versus Output Current

TYPICAL APPLICATIONS FOR NPN BRTs

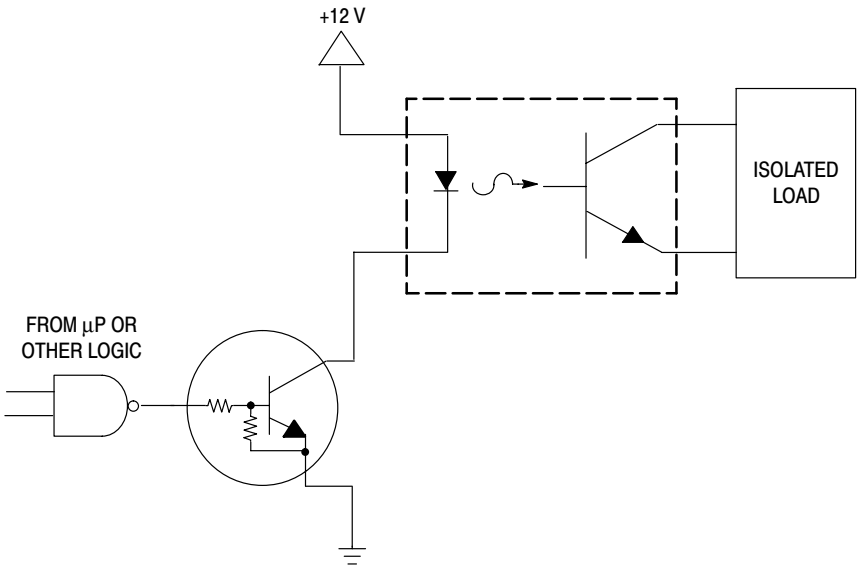


Figure 22. Level Shifter: Connects 12 or 24 Volt Circuits to Logic

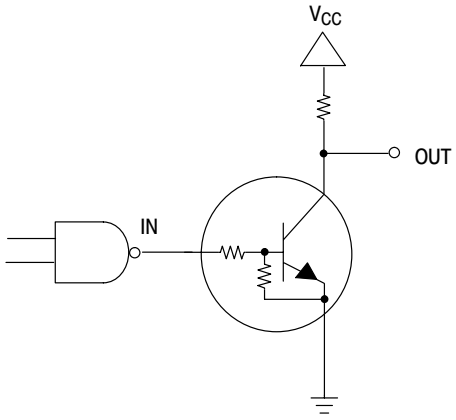


Figure 23. Open Collector Inverter: Inverts the Input Signal

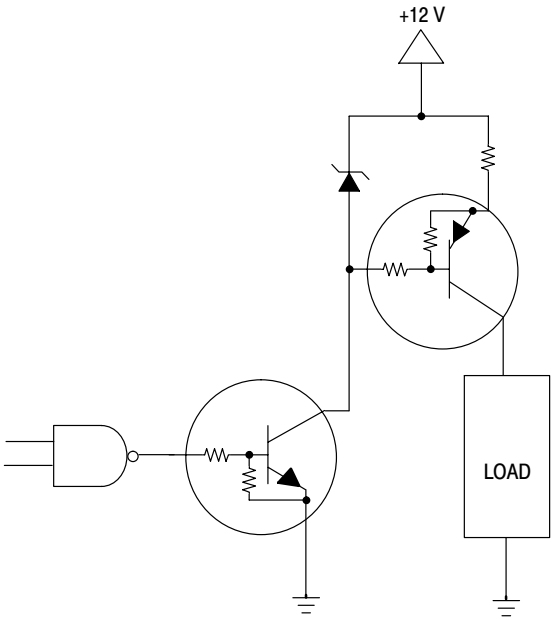


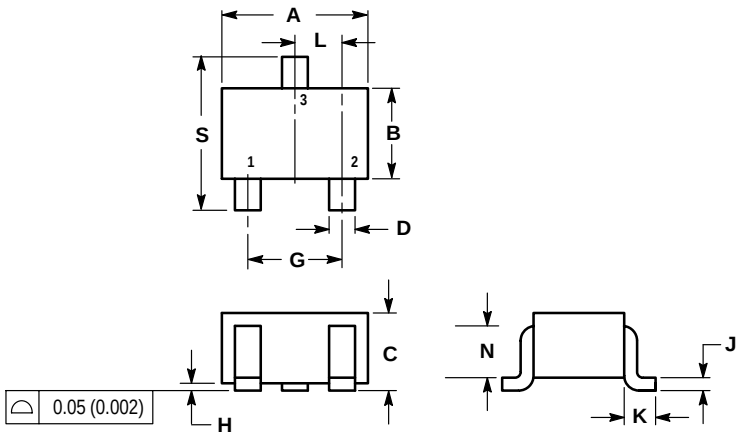
Figure 24. Inexpensive, Unregulated Current Source

PACKAGE OUTLINE & DIMENSIONS

MUN521 Series

SC−70 / SOT−323

NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.071	0.087	1.80	2.20
B	0.045	0.053	1.15	1.35
C	0.032	0.040	0.80	1.00
D	0.012	0.016	0.30	0.40
G	0.047	0.055	1.20	1.40
H	0.000	0.004	0.00	0.10
J	0.004	0.010	0.10	0.25
K	0.017 REF		0.425 REF	
L	0.026 BSC		0.650 BSC	
N	0.028 REF		0.700 REF	
S	0.079	0.095	2.00	2.40

PIN 1. BASE
2. EMITTER
3. COLLECTOR